

10-17-02

2811



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Docket No.: M-11121 US

October 14, 2002

Box NON-FEE AMENDMENT
Commissioner For Patents
Washington, D.C. 20231

Re: Applicant: Hyeon-Seag Kim
Assignee: Advanced Micro Devices, Inc.
Title: MOSFET With Buffer And Blocking Layers
Application No.: 09/877,906
Examiner: Douglas W. Owens
Docket No.: M-11121 US
Filed: June 9, 2001
Group Art Unit: 2811

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Dear Sir:

Transmitted herewith are the following documents in the above-identified application:

- (1) Return Receipt Postcard;
- (2) This Transmittal Form (1 pg) in duplicate; and
- (3) Response to Office Action (9 pgs)

☒ No additional fee is required.

CLAIMS AS AMENDED

	Claims Remaining <u>After Amendment</u>		Highest No. Previously <u>Paid For</u>		Present <u>Extra</u>	<u>Rate</u>	Additional <u>Fee</u>
Total Claims	13	Minus	20	=	0	x \$18.00	\$ 0.00
Independent Claims	2	Minus	3	=	0	x \$84.00	\$ 0.00
<input type="checkbox"/> Fee of _____ for the first filing of one or more multiple dependent claims per application							\$
<u>Total additional fee for this Amendment:</u>							\$ 0.00

- ☒ Conditional Petition for Extension of Time: If an extension of time is required for timely filing of the enclosed document(s) after all papers filed with this transmittal have been considered, an extension of time is hereby requested.
- ☒ Also, charge any additional fees required and credit any overpayment to our Deposit Account No. 19-2386.

Total: \$ 0.00

EXPRESS MAIL LABEL NO:

EV174805768 US

Respectfully submitted,

Norman R. Klivans

Norman R. Klivans
Attorney for Applicant
Reg. No. 33,003



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

#5/B
10/23/02
Jme H

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Assignee: Advanced Micro Devices, Inc.
Title: MOSFET With Buffer And Blocking Layers
Application No.: 09/877,906 Filing Date: June 09, 2001
Examiner: Owens, Douglas W. Group Art Unit: 2811
Docket No.: M-11121 US

San Jose, California
October 15, 2002

BOX NON-FEE AMENDMENT
COMMISSIONER FOR PATENTS
Washington, D. C. 20231

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RESPONSE TO OFFICE ACTION

Dear Sir:

This paper is a response to an Office Action dated July 31, 2002, in this case. Please enter the following amendments.

IN THE SPECIFICATION

Please replace paragraph [0010] beginning on page 2, with the following replacement paragraph. In accordance with 37 C.F.R §1.121 (b)(1)(iii), a marked-up version of the replacement paragraph with markings to show changes made, is included in Appendix A, attached.

[0010] In FIG. 3, a high k dielectric layer 21 is grown over the substrate including the implanted channel. High k dielectric layer may be, for example, a metal oxide, such as, for example, zircon oxide, titanium oxide, tantalum oxide, or hafnium oxide. The high k dielectric layer is grown epitaxially as illustrated in FIG. 9. The high k dielectric layer includes alternating monolayers of oxygen 21a and metal 21b. Epitaxial high k dielectric layer 21, and other epitaxial layers described below, may be grown, for example, by

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